

N-Channel Power MOSFET

700V, 4.5A, 0.9Ω

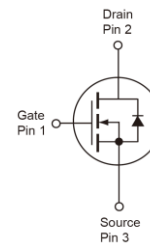
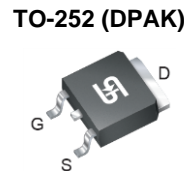
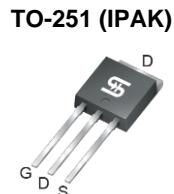
FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

APPLICATION

- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	700	V
$R_{DS(on)}$ (max)	0.9	Ω
Q_g	9.7	nC



Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (DPAK) per J-STD-020.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT
Drain-Source Voltage	V_{DS}	700		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current ^(Note 1)	I_D	$T_C = 25^\circ\text{C}$	4.5	A
		$T_C = 100^\circ\text{C}$	2.7	
Pulsed Drain Current ^(Note 2)	I_{DM}	13.5		A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	50	20	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	64		mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	1.6		A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150		°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	2.5	6.25	°C/W
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62		°C/W

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.

ELECTRICAL SPECIFICATIONS ($T_C = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	700	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2.0	3.1	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.5A$	$R_{DS(on)}$	--	0.83	0.9	Ω
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 380V, I_D = 2.3A,$ $V_{GS} = 10V$	Q_g	--	9.7	--	nC
Gate-Source Charge		Q_{gs}	--	2.9	--	
Gate-Drain Charge		Q_{gd}	--	3.5	--	
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	482	--	pF
Output Capacitance		C_{oss}	--	34	--	
Gate Resistance	$F = 1MHz, \text{open drain}$	R_g	--	3.6	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 40\Omega,$ $I_D = 2.3A, V_{GS} = 10V,$	$t_{d(on)}$	--	20	--	ns
Turn-On Rise Time		t_r	--	54	--	
Turn-Off Delay Time		$t_{d(off)}$	--	34	--	
Turn-Off Fall Time		t_f	--	48	--	
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 4.5A, V_{GS} = 0V$	V_{SD}	--	--	1.4	V
Reverse Recovery Time	$V_R = 200V, I_S = 2.3A$ $di_f/dt = 100A/\mu s$	t_{rr}	--	176	--	ns
Reverse Recovery Charge		Q_{rr}	--	1.1	--	μC

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 50mH, I_{AS} = 1.6A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu s, \text{duty cycle} \leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM70N900CI C0G	ITO-220	50pcs / Tube
TSM70N900CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N900CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

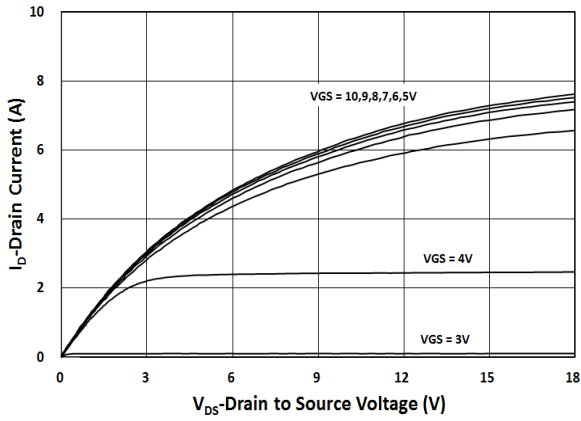
Note:

1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

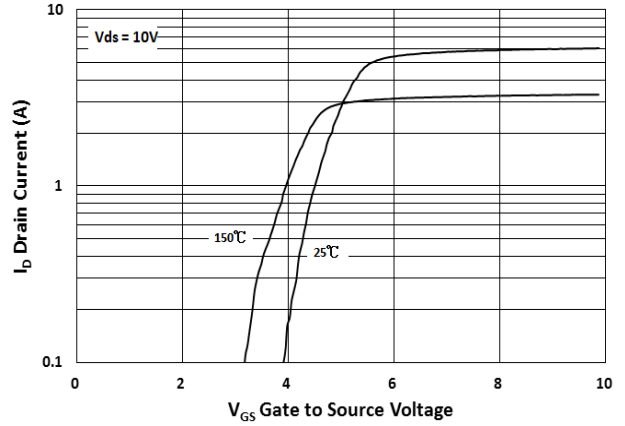
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

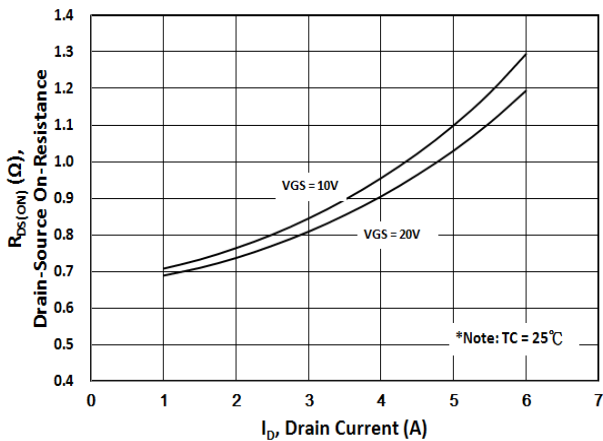
Output Characteristics



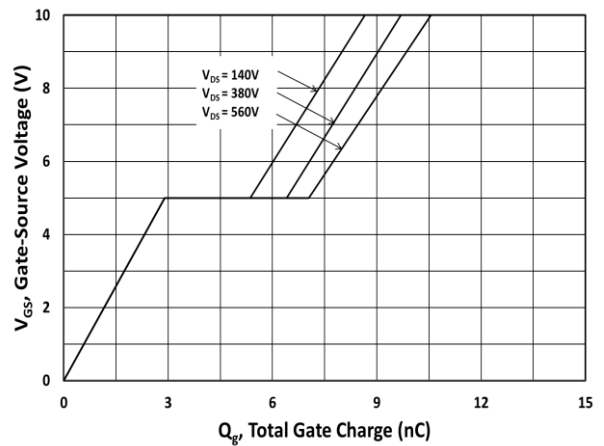
Transfer Characteristics



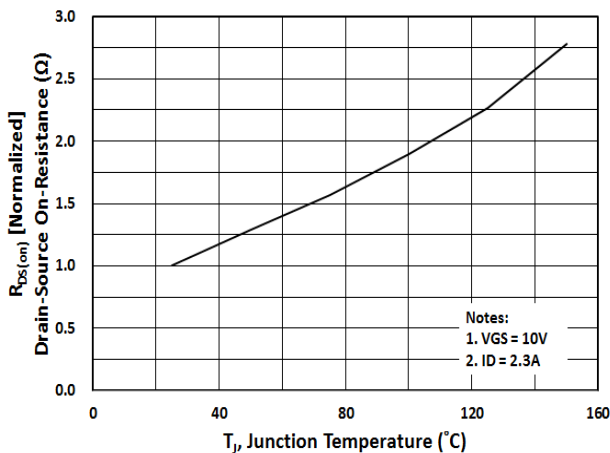
On-Resistance vs. Drain Current



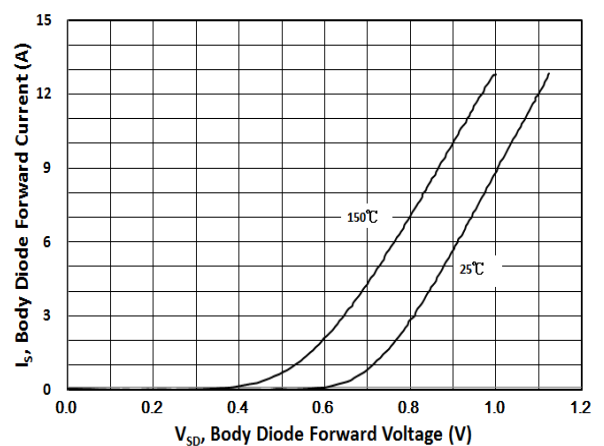
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



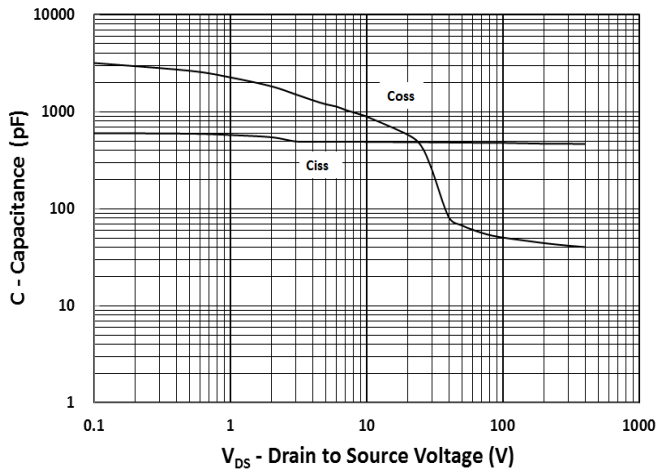
Source-Drain Diode Forward Current vs. Voltage



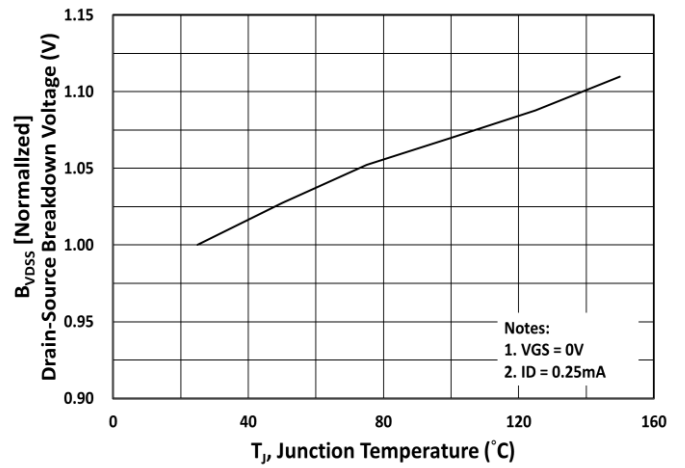
CHARACTERISTICS CURVES

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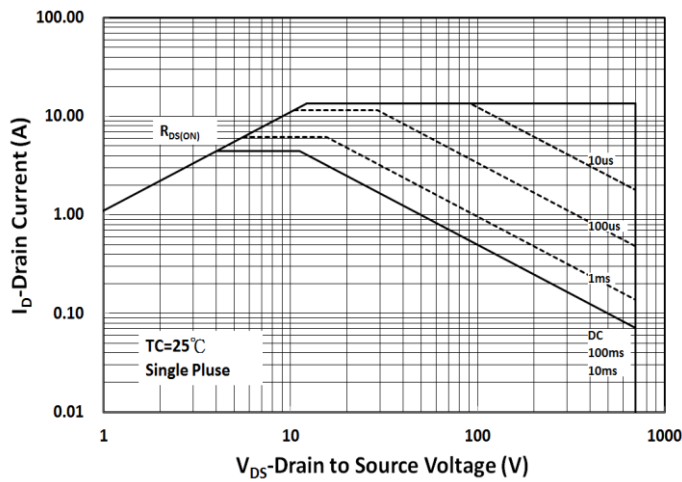
Capacitance vs. Drain-Source Voltage



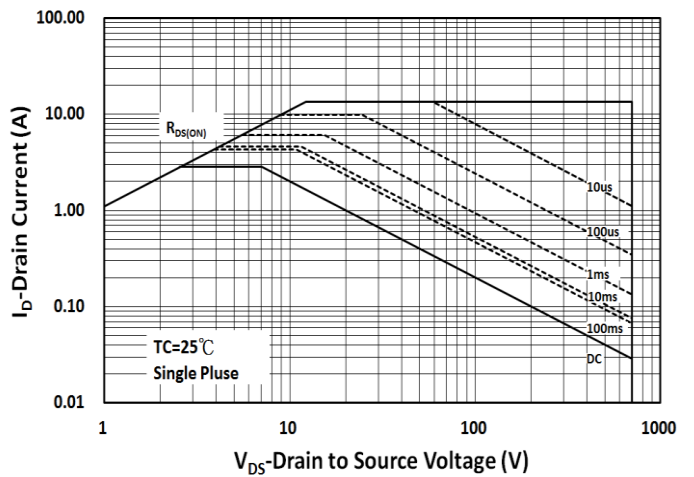
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (DPAK/IPAK)



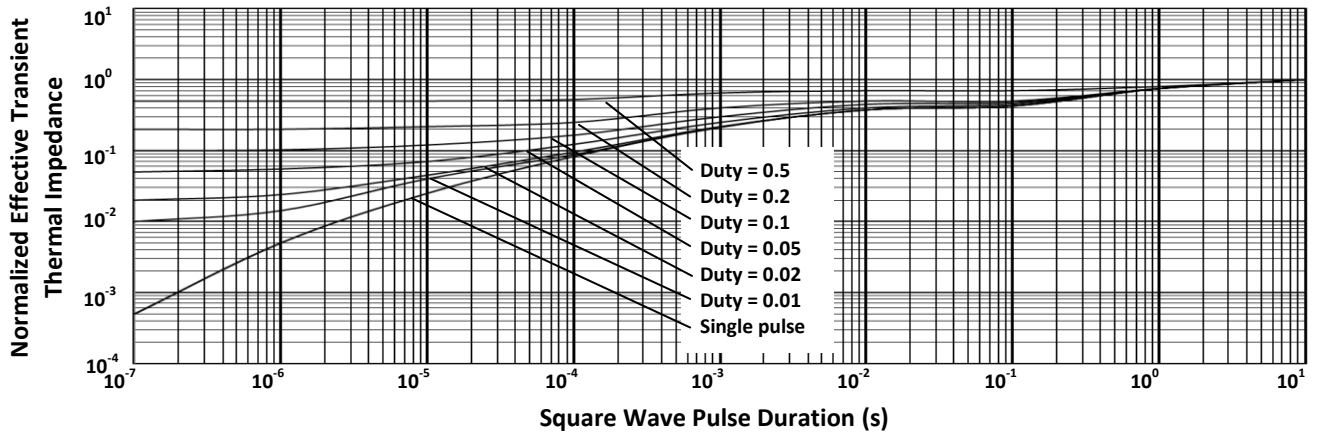
Maximum Safe Operating Area (ITO-220)



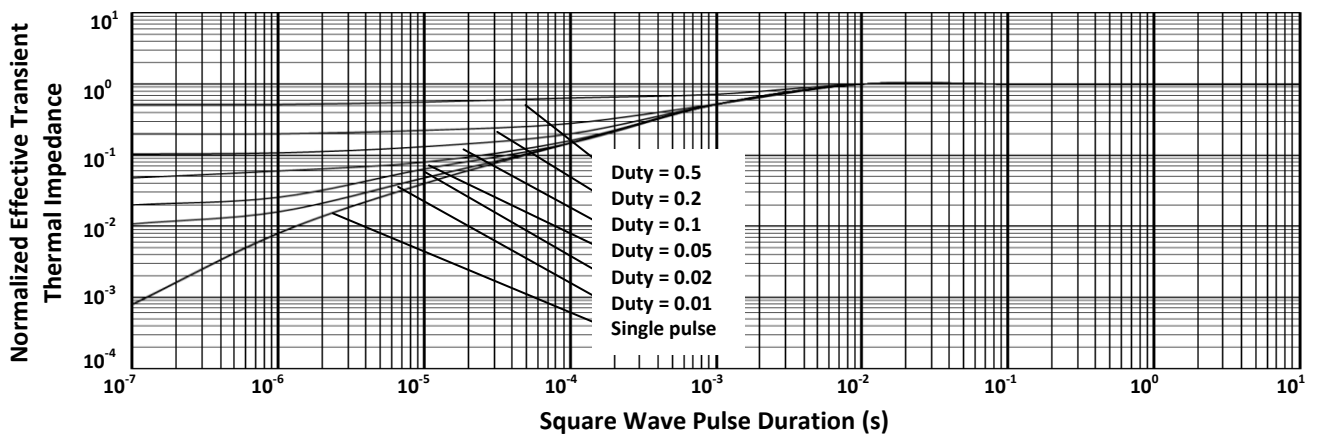
ELECTRICAL CHARACTERISTICS CURVES

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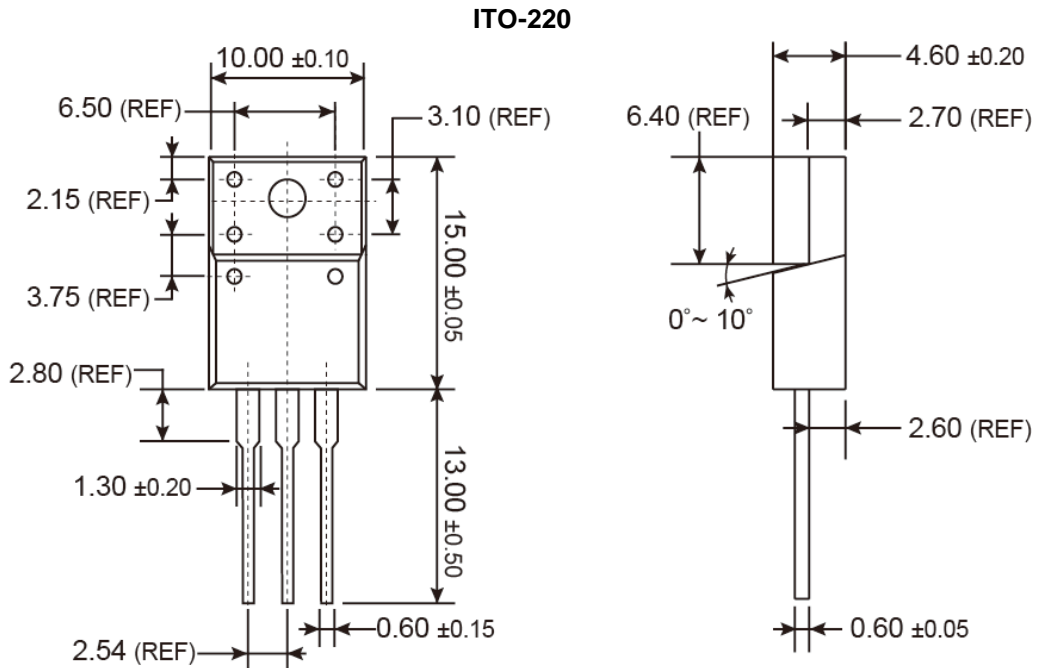
Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)



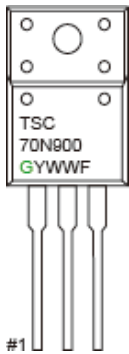
Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

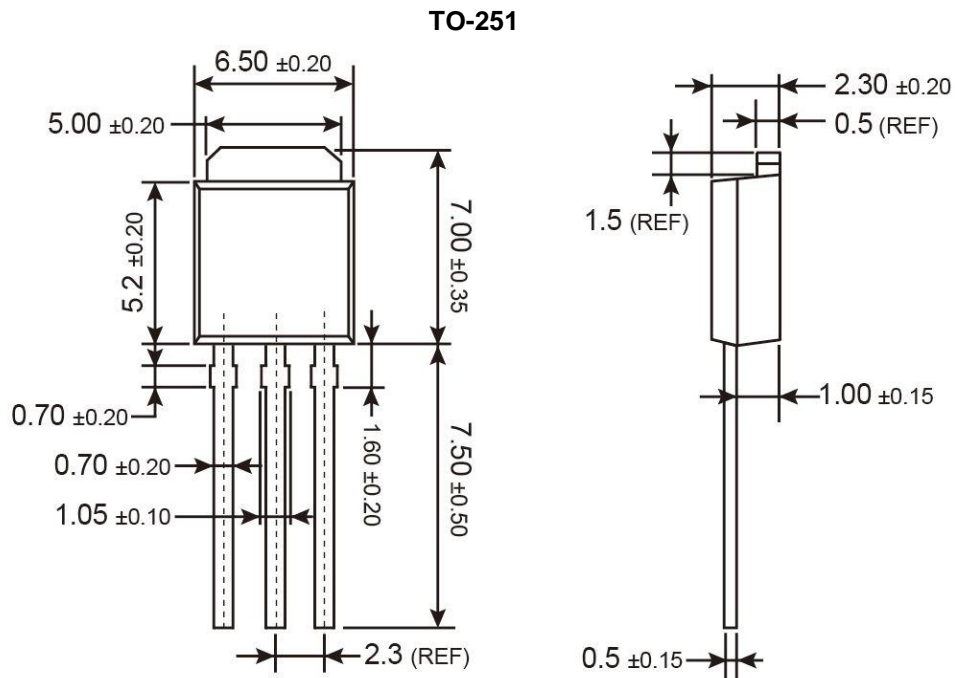


MARKING DIAGRAM

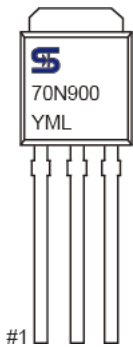


- G** = Halogen Free
- Y** = Year Code
- WW** = Week Code (01~52)
- F** = Factory Code

PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

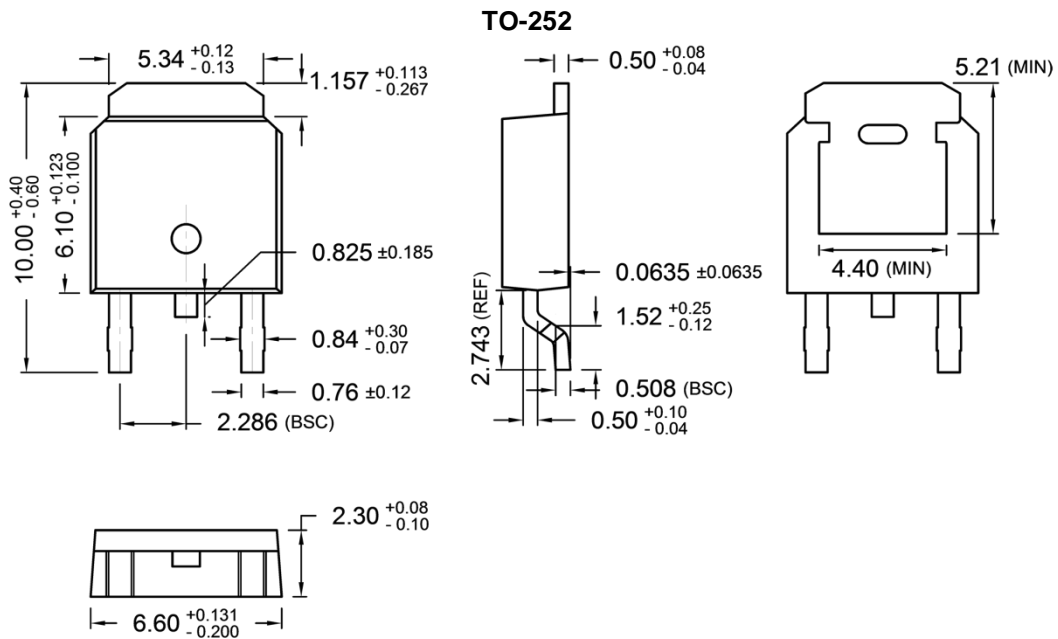


MARKING DIAGRAM

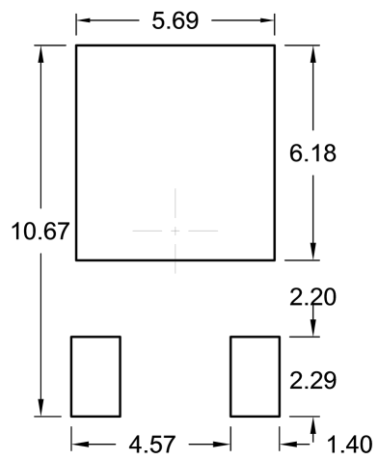


- Y** = Year Code
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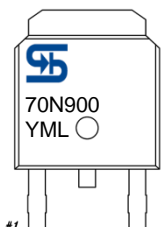
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



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